TOSHIBA Transistor Silicon NPN Triple Diffused Type

2SD2012

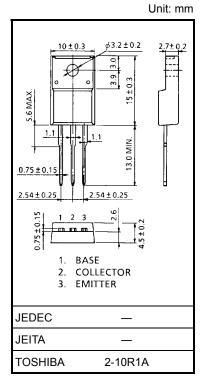
Audio Frequency Power Amplifier Applications

• High DC current gain: $h_{FE} (1) = 100 (min)$

- Low saturation voltage: VCE (sat) = 1.0 V (max)
- High power dissipation: PC = 25 W (Tc = 25°C)

Maximum Ratings (Tc = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	60	V	
Collector-emitter voltage		V _{CEO}	60	V	
Emitter-base voltage		V _{EBO}	7	V	
Collector current		Ι _C	3	А	
Base current		Ι _Β	0.5	А	
Collector power dissipation	Ta = 25°C	Pc	2.0	w	
	Tc = 25°C		25		
Junction temperature		Тј	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

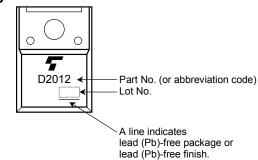


Electrical Characteristics (Tc = 25°C)

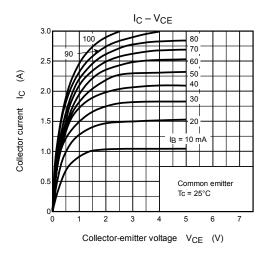
Weight: 1.7 g (typ.)

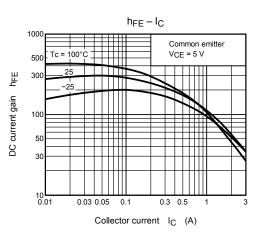
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 60 V, I _E = 0	_	_	100	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 7 V, I _C = 0	-	_	100	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 50 mA, I _B = 0	60	_	_	V
DC current gain	h _{FE (1)}	V _{CE} = 5 V, I _C = 0.5 A	100	_	320	
	h _{FE (2)}	V _{CE} = 5 V, I _C = 2 A	20	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 2 A, I _B = 0.2 A	_	0.4	1.0	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 0.5 A	_	0.75	1.0	V
Transition frequency	f _T	V _{CE} = 5 V, I _C = 0.5 A	_	3	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	35	_	pF

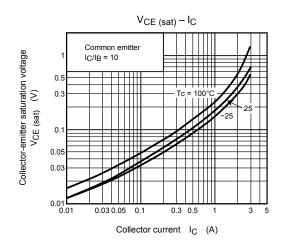
Marking

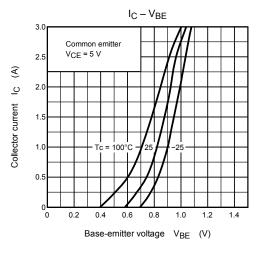


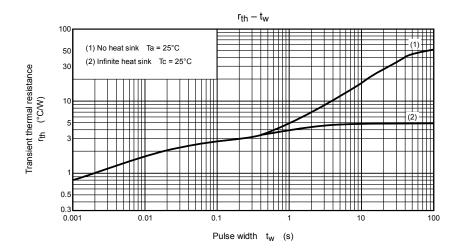
TOSHIBA

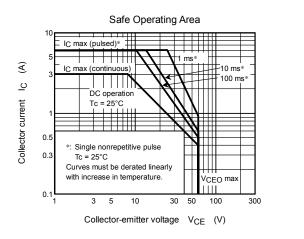


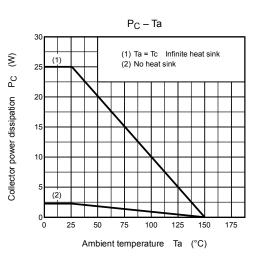












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